

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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ITC1100 1000 WATT, 50V, Pulsed Avionics 1030 MHz

GENERAL DESCRIPTION

The ITC1100 is a common base bipolar transistor. It is designed for pulsed interrogator systems in the frequency band of 1030 MHz. The device has gold thin-film metallization for proven high MTTF. The transistor includes input returns for improved output rise time . Low thermal resistance package reduces junction temperature which extends the life time of the product.

CASE OUTLINE 55SW, Style 1 Common Base

ABSOLUTE MAXIMUM RATINGS

Power Dissipation

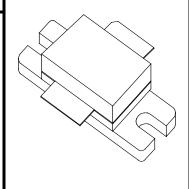
Device Dissipation¹ @25°C (P_d) 3400 W Thermal Resistance¹ (θ_{IC}) .08°C/W

Voltage and Current

Collector-Base Voltage 65V Emitter-Base Voltage 3.5V Collector Current¹ 80A

Temperatures

Storage Temperature $-40 \text{ to } +150^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BVebo ²	Emitter-Base Breakdown(open)	Ie=50mA	3.5			V
BVces	Collector-Emitter Breakdown(shorted)	Ic=30mA	65			V
BVceo ²	Collector-Emitter Breakdown (open)	Ic=30mA	30			V
h _{FE} ²	DC Current Gain	Ic=5A, Vce=5V	20		100	β

FUNCTIONAL CHARACTERISTICS @ 25°C

G_{PB}	Common Base Power Gain	$V_{cc} = 50V, F = 1030MHz,$	10	10.5		dB
		P _{out} =1000W Peak Min, PW=1µS, DF=1%				
$\eta_{ m c}$	Collector Efficiency	$V_{cc} = 50V, F = 1030MHz,$	45	50		%
10		P _{out} =1000W Peak Min, PW=1µS, DF=1%				
t _r	Rise Time	$V_{cc} = 50V, F = 1030MHz,$		50	80	nS
		P _{out} =1000W Peak Min, PW=1μS, DF=1%				
VSWR	Output Load Mismatch	$V_{cc} = 50V, F = 1030MHz,$			4:1	Ψ
		P _{out} =1000W Peak Min, PW=1μS, DF=1%				
Z_{in}	Series Input Impedance (Circuit	$V_{cc} = 50V, F = 1030MHz,$	0.89 - j2.3		3	Ω
	source impedance @ test cond.)	P _{out} =1000W Peak Min, PW=1µS, DF=1%				
Z_{out}	Series Output Impedance (Circuit	$V_{cc} = 50V, F = 1030MHz,$	0.54 - j2.64		Ω	
out	load impedance @ test cond.)	P _{out} =1000W Peak Min, PW=1μS, DF=1%		3		

At rated output power and pulse conditions

² Not measurable due to EB Returns

